Elektronische Bauelemente

SSG08N10-C

8A, 100V, $R_{DS(ON)}$ 24mΩ
N-Ch Enhancement Mode Power MOSFET

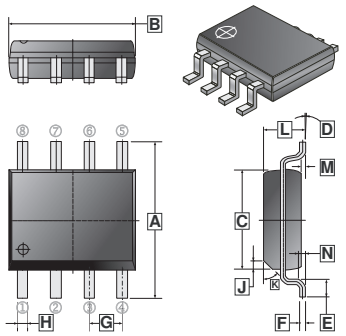
RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

DESCRIPTION

The SSG08N10-C is the highest performance trench N-ch MOSFETs with extreme high cell density, which provide excellent R_{DSON} and gate charge for most of the synchronous buck converter applications .

The SSG08N10-C meet the RoHS and Green Product requirement with full function reliability approved.

SOP-8



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	5.79	6.20	H	0.33	0.51
B	4.70	5.11	J	0.375 REF.	
C	3.80	4.00	K	45°REF.	
D	0°	8°	L	1.3	1.752
E	0.40	1.27	M	0	0.25
F	0.10	0.25	N	0.25 REF.	
G	1.27 TYP.				

FEATURES

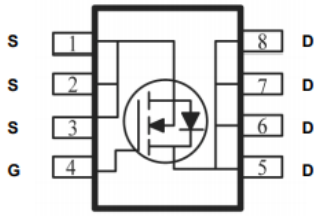
- Advanced high cell density Trench technology
- Super Low Gate Charge
- Green Device Available

PACKAGE INFORMATION

Package	MPQ	Leader Size
SOP-8	2.5K	13 inch

ORDER INFORMATION

Part Number	Type
SSG08N10-C	Lead (Pb)-free and Halogen-free



ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise specified)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current [1] @ V_{GS}=10V	T_A=25°C	I_D	8	A
	T_A=100°C		6.6	
Pulsed Drain Current [2]		I_{DM}	32	A
Power Dissipation [3]	T_A=25°C	P_D	2.7	W
Operating Junction & Storage Temperature Range		T_J, T_{STG}	-55~150	°C
Thermal Resistance Rating				
Thermal Resistance Junction-Ambient [1]		$R_{\theta JA}$	t≦10s, 45	°C/W
		$R_{\theta JA}$	Steady State ,80	°C/W

ELECTRICAL CHARACTERISTICS (T_J=25°C unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-Source Breakdown Voltage	BV_{DSS}	100	-	-	V	V_{GS}=0V, I_D=250μA
Gate-Threshold Voltage	$V_{GS(th)}$	1.2	-	2.5	V	V_{DS}=V_{GS}, I_D=250μA
Gate-Source Leakage Current	I_{GSS}	-	-	±100	nA	V_{GS}=±20V
Drain-Source Leakage Current	I_{DSS}	-	-	1	μA	V_{DS}=80V,V_{GS}=0, T_J=25°C
		-	-	5		V_{DS}=80V,V_{GS}=0, T_J=55°C
Drain-Source On-Resistance [2]	$R_{DS(ON)}$	-	-	24	mΩ	V_{GS}=10V, I_D=8A
		-	-	28		V_{GS}=4.5V, I_D=4A
Total Gate Charge	Q_g	-	57	-	nC	I_D=8A V_{DS}=30V V_{GS}=10V
Gate-Source Charge	Q_{gs}	-	8.7	-		
Gate-Drain Charge	Q_{gd}	-	14	-		
Turn-On Delay Time	$T_{d(on)}$	-	16.2	-	nS	V_{DD}=30V I_D=1A V_{GS}=10V R_G=3.3Ω
Rise Time	T_r	-	41.2	-		
Turn-Off Delay Time	$T_{d(off)}$	-	56.4	-		
Fall Time	T_f	-	16.2	-		
Input Capacitance	C_{iss}	-	3307	-	pF	V_{GS}=0V V_{DS}=25V f=1.0MHz
Output Capacitance	C_{oss}	-	201	-		
Reverse Transfer Capacitance	C_{rss}	-	151	-		
Source-Drain Diode						
Continuous Source Current [1]	I_S	-	-	8	A	
Pulsed Source Current [2]	I_{SM}	-	-	32	A	
Forward On Voltage [2]	V_{SD}	-	-	1.2	V	I_S=1A, V_{GS}=0V, T_J=25°C
Reverse Recovery Time	T_{rr}	-	44	-	nS	I_S=8A, V_{GS}=0, dI/dt=100A/μs
Reverse Recovery Charge	Q_{rr}	-	25	-	nC	

Notes:
1. Surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.
2. The data tested by pulsed, pulse width ≦ 300us, duty cycle ≦ 2%.
3. The power dissipation is limited by 150°C junction temperature.

CHARACTERISTICS CURVE

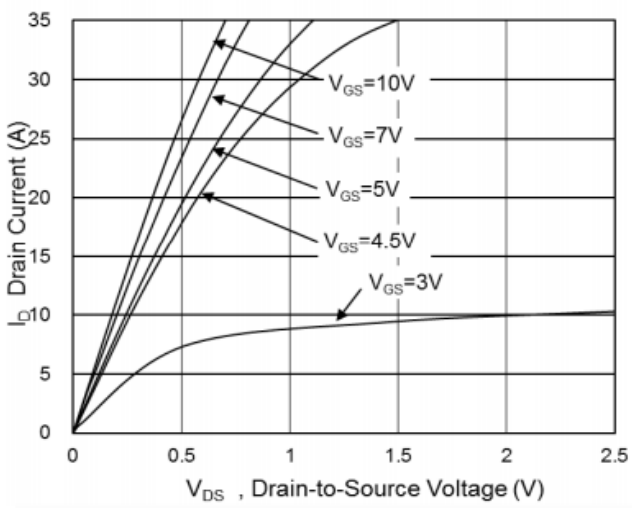


Fig.1 Typical Output Characteristics

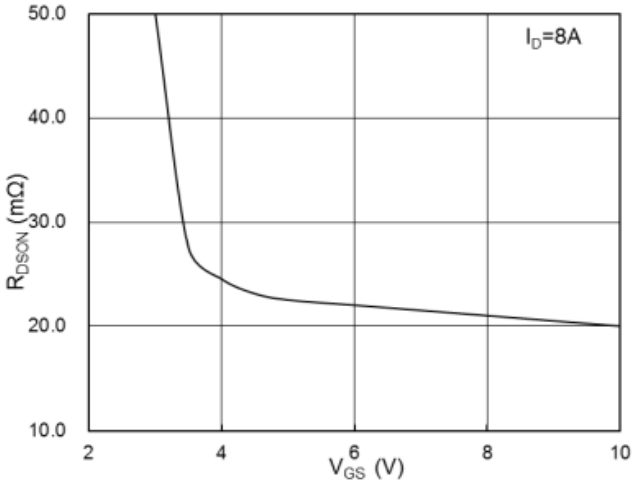


Fig.2 On-Resistance vs. G-S Voltage

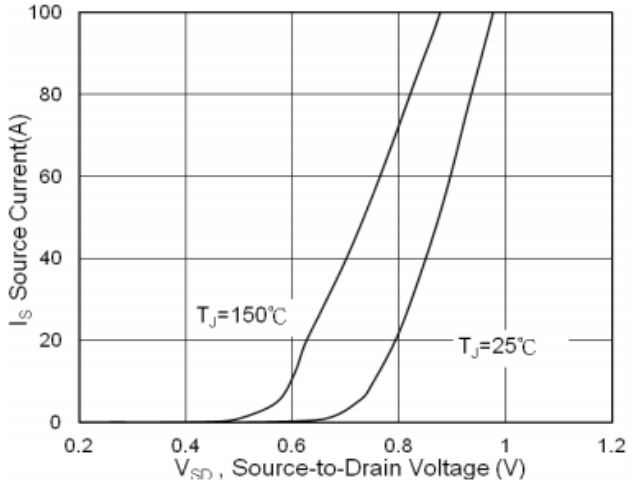


Fig.3 Source-Drain Diode Forward Voltage

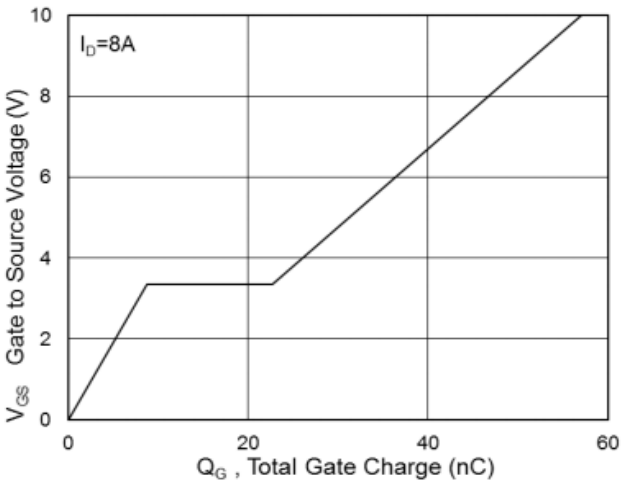


Fig.4 Gate-Charge Characteristics

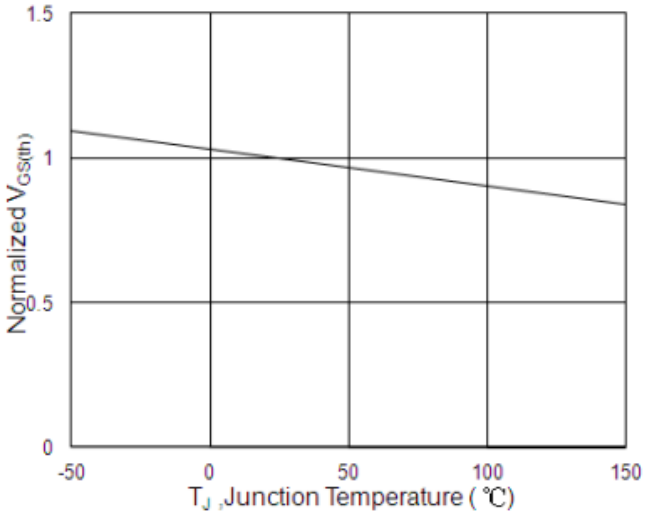


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

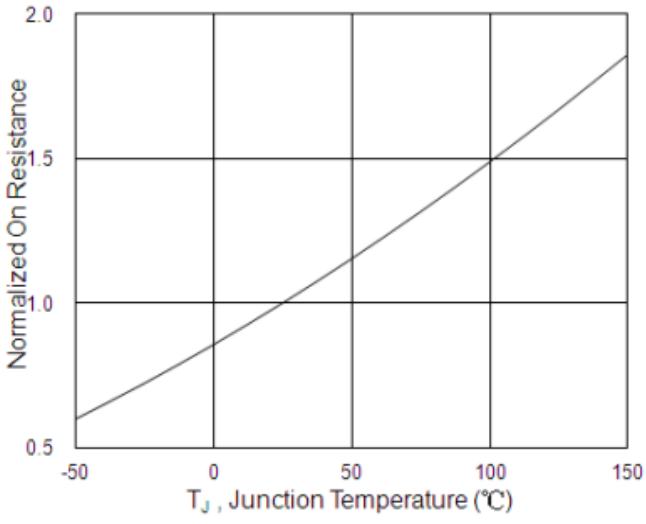


Fig.6 Normalized R_{DSON} vs. T_J

CHARACTERISTICS CURVE

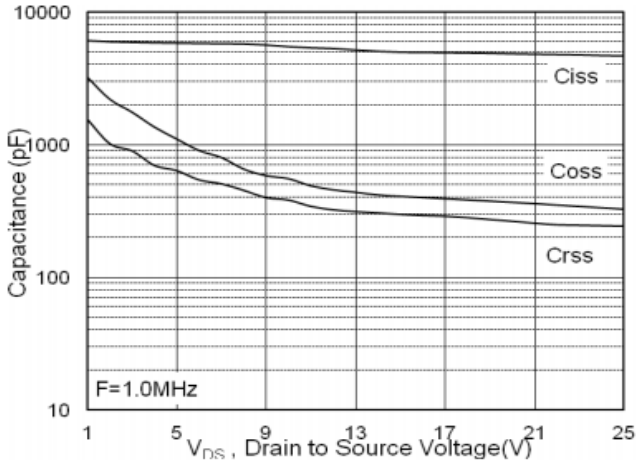


Fig.7 Capacitance

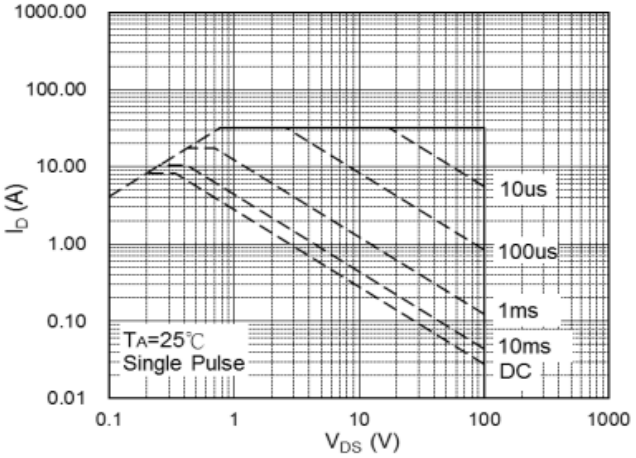


Fig.8 Safe Operating Area

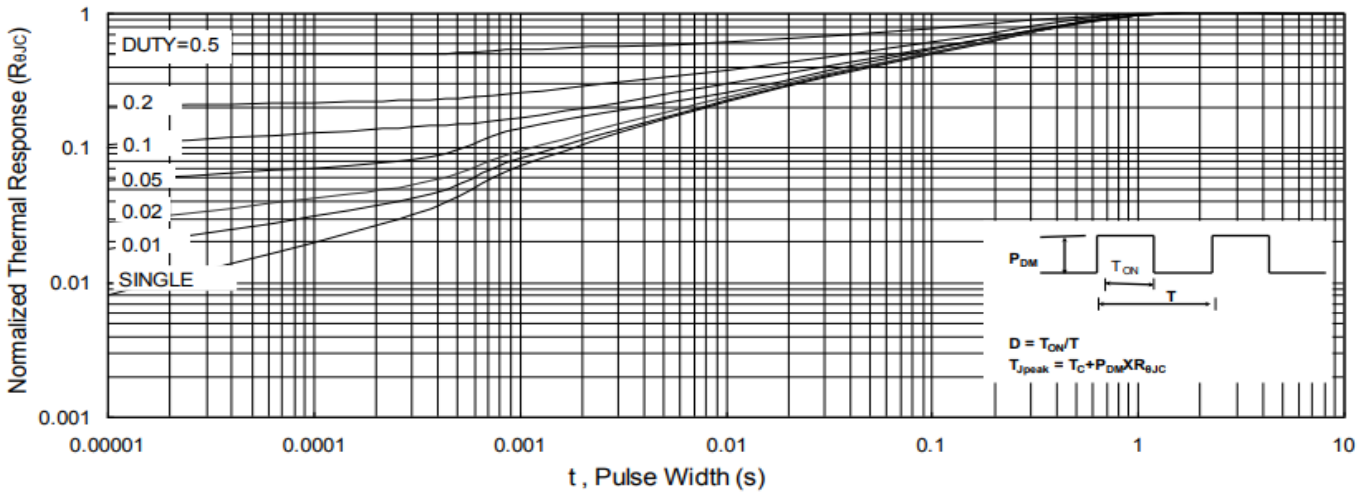


Fig.9 Normalized Maximum Transient Thermal Impedance

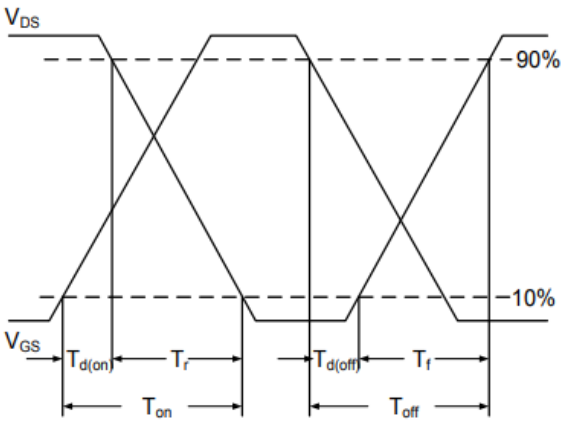


Fig.10 Switching Time Waveform

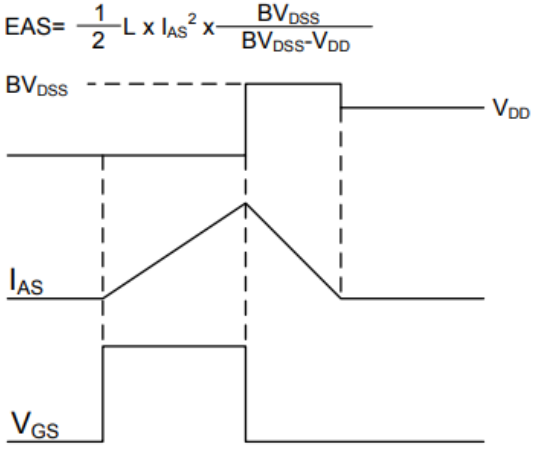


Fig.11 Unclamped Inductive Switching Waveform